

# HAT2198R

## Silicon N Channel Power MOS FET Power Switching

REJ03G0062-0200

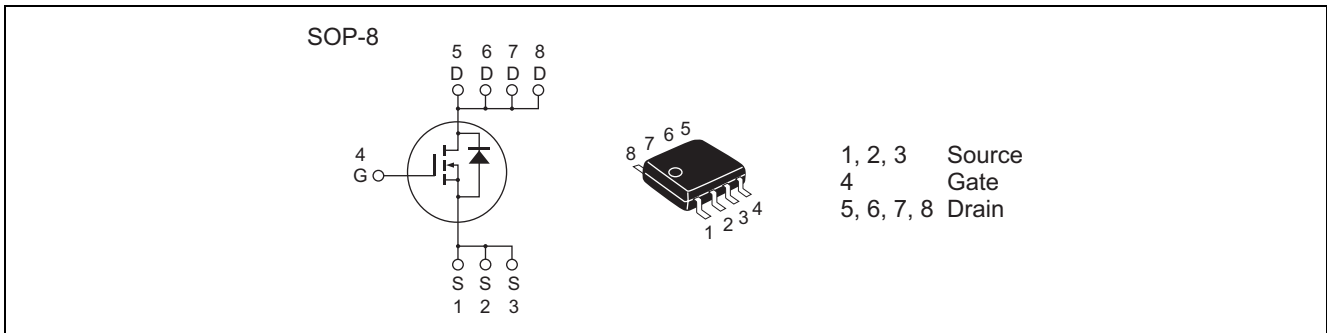
Rev.2.00

Oct.18.2004

### Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  
 $R_{DS(on)} = 7.2 \text{ m}\Omega$  typ. (at  $V_{GS} = 10 \text{ V}$ )

### Outline



### Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	30	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	14	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	112	A
Body-drain diode reverse drain current	$I_{DR}$	14	A
Avalanche current	$I_{AP}$ <sup>Note 2</sup>	14	A
Avalanche energy	$E_{AR}$ <sup>Note 2</sup>	19.6	mJ
Channel dissipation	$P_{ch}$ <sup>Note3</sup>	2.5	W
Channel to ambient thermal impedance	$\theta_{ch-a}$ <sup>Note3</sup>	50	$^\circ\text{C}/\text{W}$
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Notes: 1.  $PW \leq 10 \mu\text{s}$ , duty cycle  $\leq 1\%$

2. Value at  $T_{ch} = 25^\circ\text{C}$ ,  $R_g \geq 50 \Omega$

3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm),  $PW \leq 10\text{s}$

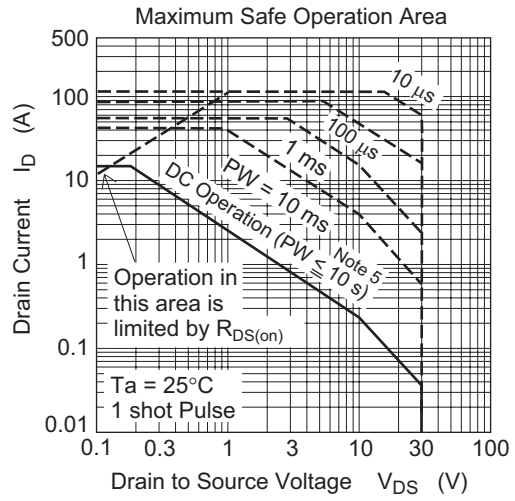
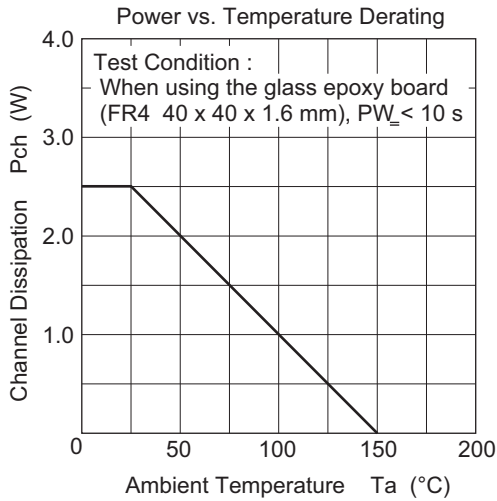
## Electrical Characteristics

(Ta = 25°C)

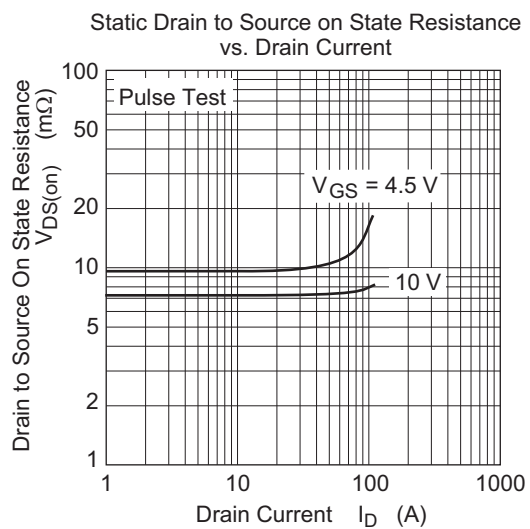
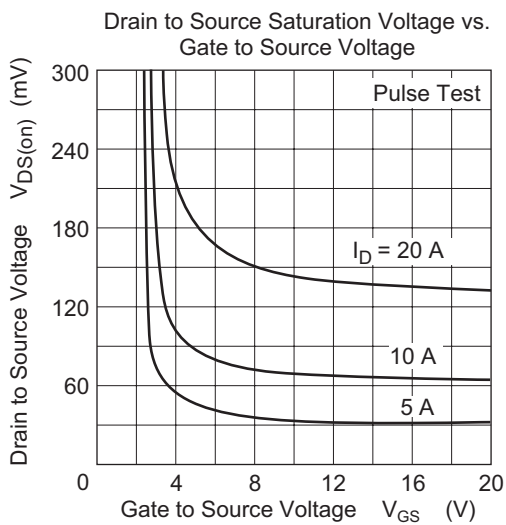
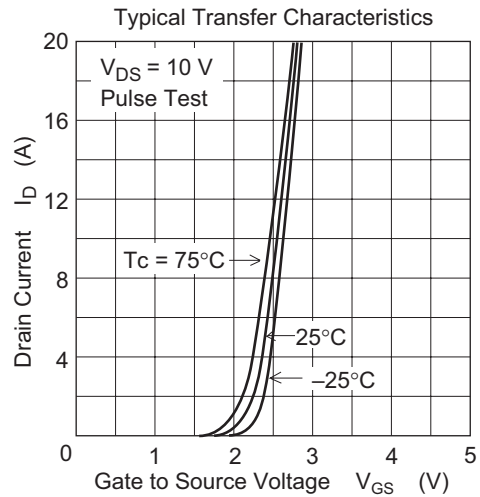
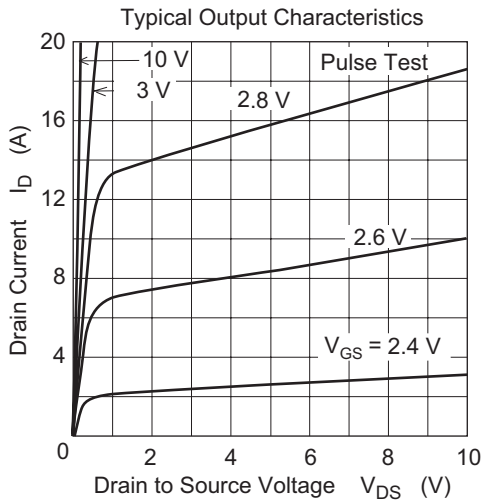
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	7.2	9.0	$\text{m}\Omega$	$I_D = 7 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
	$R_{DS(on)}$	—	9.6	14.0	$\text{m}\Omega$	$I_D = 7 \text{ A}$ , $V_{GS} = 4.5 \text{ V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	18	30	—	S	$I_D = 7 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	1650	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	$C_{oss}$	—	390	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	135	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	$R_g$	—	0.55	—	$\Omega$	
Total gate charge	$Q_g$	—	11	—	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	$Q_{gs}$	—	4.7	—	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	$Q_{gd}$	—	2.5	—	nC	$I_D = 14 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	8.5	—	ns	$V_{GS} = 10 \text{ V}$ , $I_D = 7 \text{ A}$
Rise time	$t_r$	—	5	—	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	38	—	ns	$R_L = 1.42 \Omega$
Fall time	$t_f$	—	3.8	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$	—	0.80	1.04	V	$I_F = 14 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-drain diode reverse recovery time	$t_{rr}$	—	28	—	ns	$I_F = 14 \text{ A}$ , $V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu\text{s}$

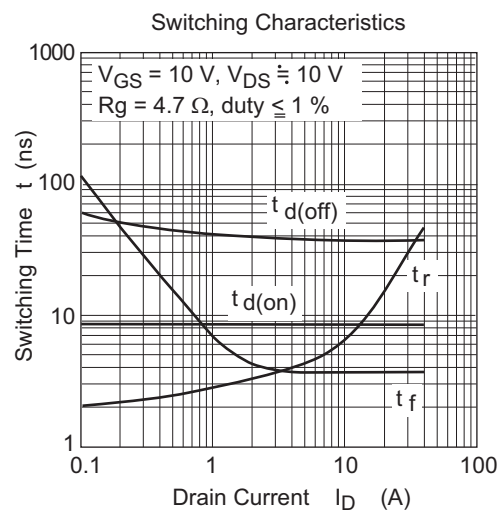
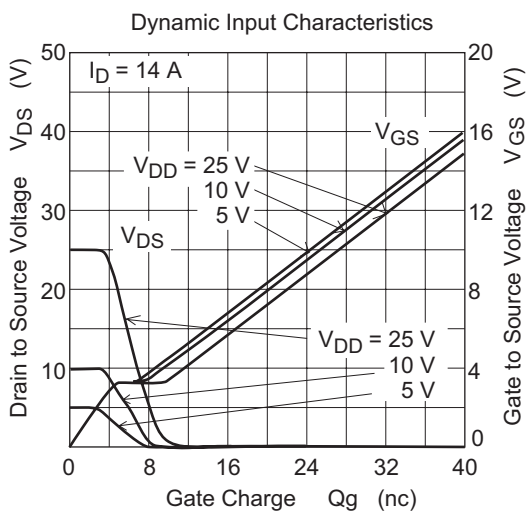
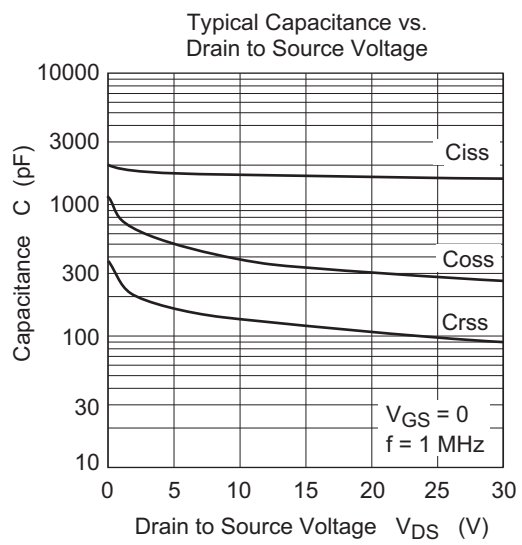
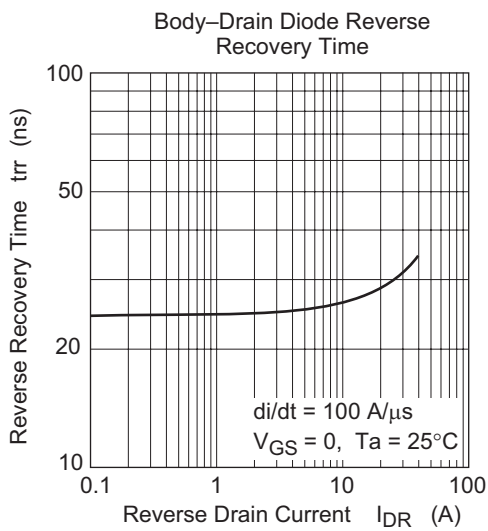
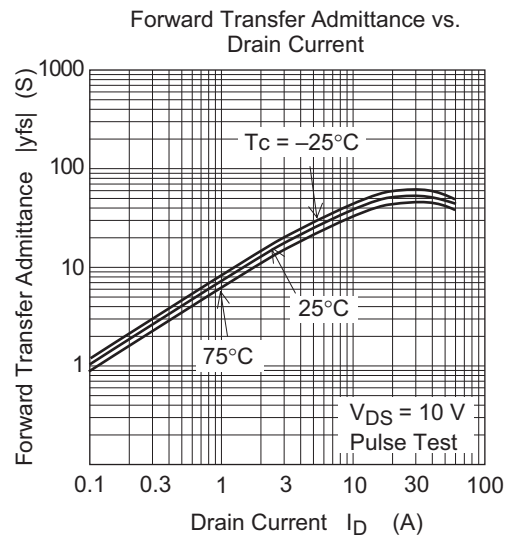
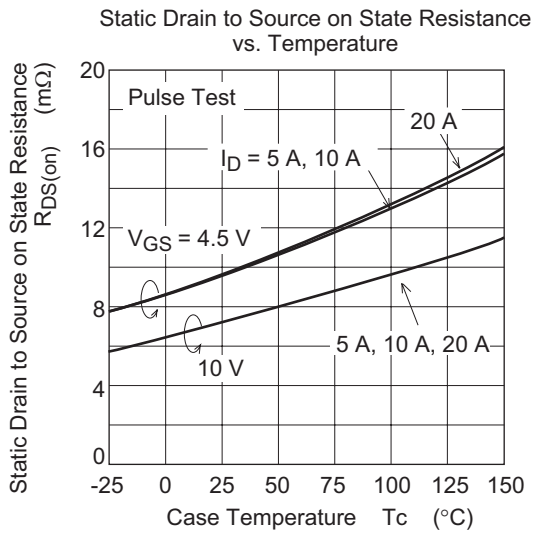
Notes: 4. Pulse test

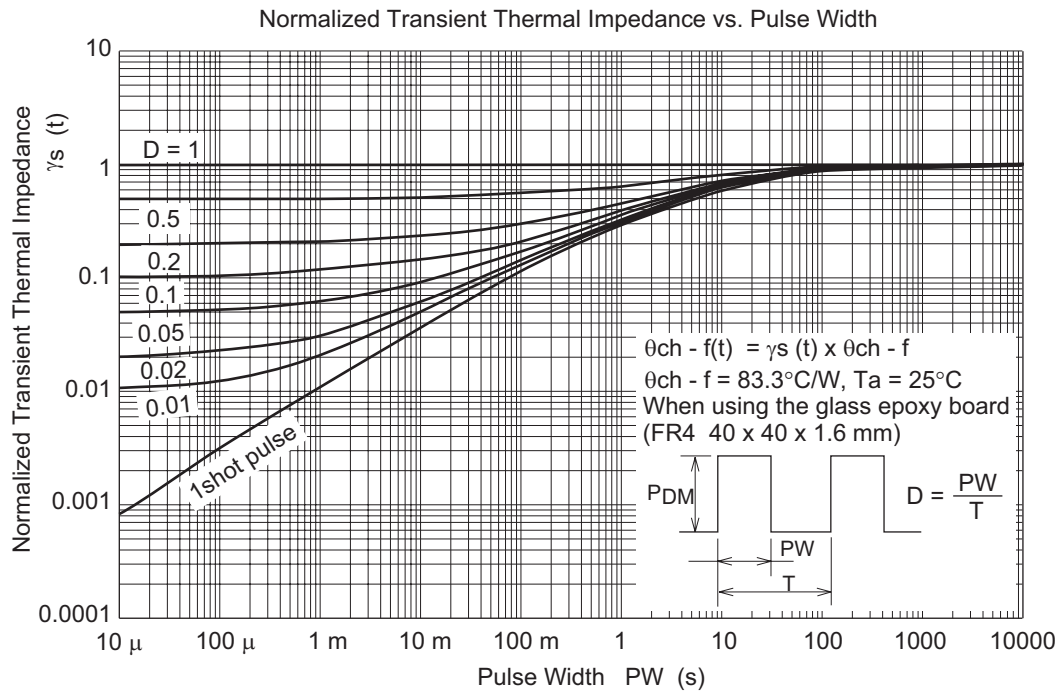
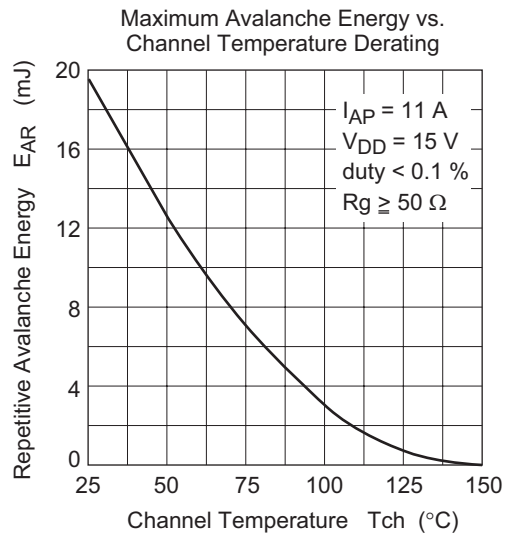
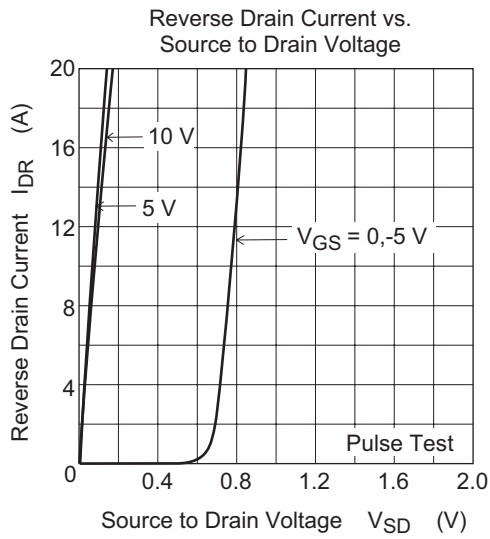
Main Characteristics



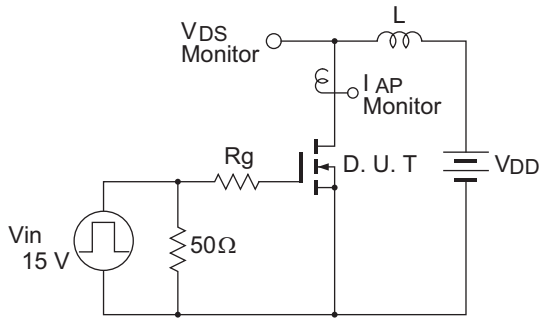
Note 5 :  
When using the glass epoxy board  
(FR4 40x40x1.6 mm)





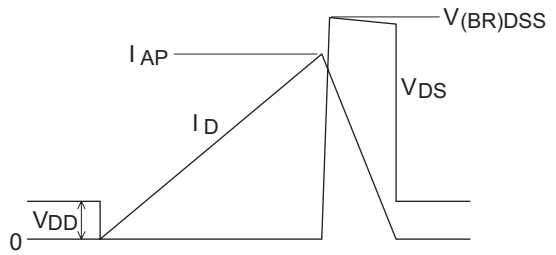


Avalanche Test Circuit

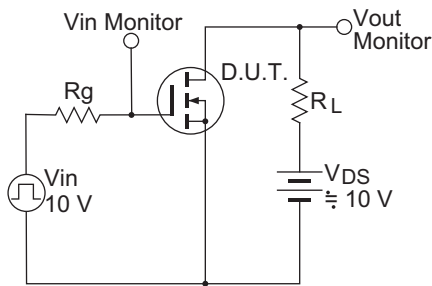


Avalanche Waveform

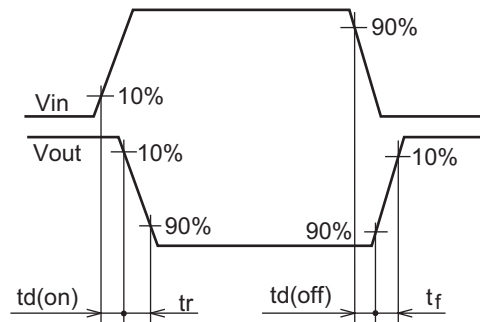
$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Switching Time Test Circuit

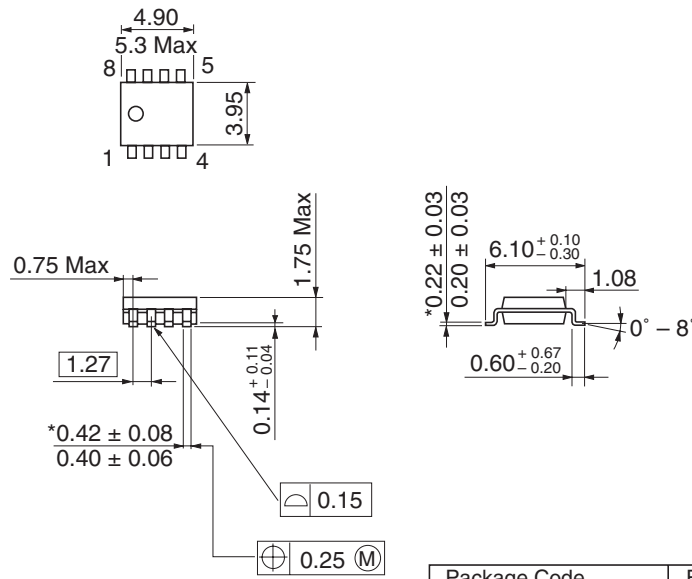


Switching Time Waveform



### Package Dimensions

As of January, 2003  
Unit: mm



\*Dimension including the plating thickness  
Base material dimension

Package Code	FP-8DA
JEDEC	Conforms
JEITA	—
Mass (reference value)	0.085 g

### Ordering Information

Part Name	Quantity	Shipping Container
HAT2198R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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